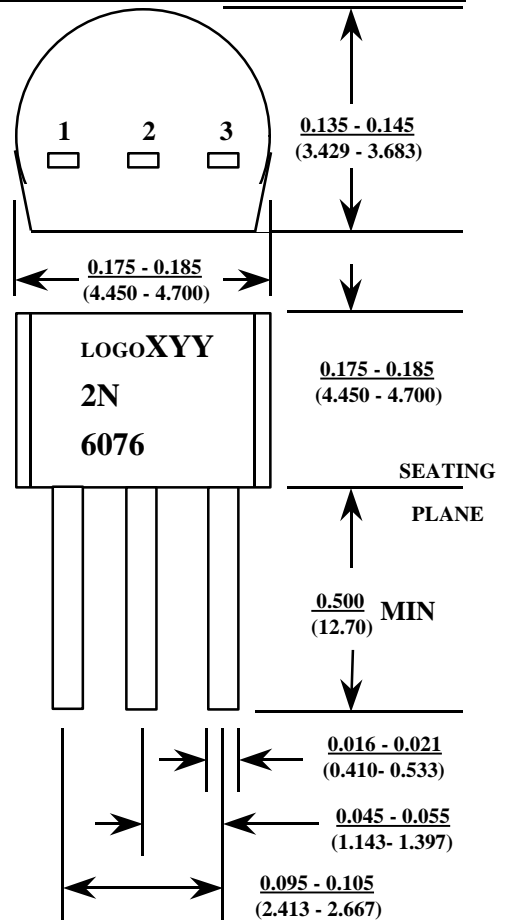
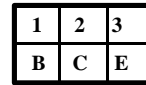


# 2N6076

## SILICON PNP SMALL SIGNAL TRANSISTOR

$BV_{CEO} \dots 25 \text{ V (Min)}$

$h_{FE} \dots 100 \text{ (Min) @ } V_{CE} = 10 \text{ V, } I_C = 10 \text{ mA}$



### ABSOLUTE MAXIMUM RATINGS (NOTE 1) TEMPERATURES

Storage Temperature	-55 Degrees C to	150 Degrees C
Operating Junction Temperature		150 Degrees C

### POWER DISSIPATION (NOTES 2 & 3)

Total Device Dissipation at $T_A = 25 \text{ Deg C}$	625 mW
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### VOLTAGES & CURRENT

$V_{CEO}$	Collector to Emitter	25 V
$V_{CBO}$	Collector to Base	25 V
$V_{EBO}$	Emitter to Base	5 V
$I_C$	Collector Current	500 mA

### ELECTRICAL CHARACTERISTICS (25 Degrees C Ambient Temperature unless otherwise stated)

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
$BV_{CBO}$	Collector to Base Voltage	25		V	$I_C = 100 \text{ uA}$
$BV_{CEO}$	Collector to Emitter Voltage	25		V	$I_C = 10 \text{ mA}$
$BV_{EBO}$	Emitter to Base Voltage	5		V	$I_E = 10 \text{ uA}$
$I_{CBO}$	Collector Cutoff Current		100	nA	$V_{CB} = 25 \text{ V}$
			10	uA	$V_{CB} = 25 \text{ V, } T = +100^\circ\text{C}$
$I_{CES}$	Collector Cutoff Current		100	nA	$V_{CE} = 25 \text{ V}$
$I_{EBO}$	Emitter Cutoff Current		100	uA	$V_{EB} = 3.0 \text{ V}$
$h_{FE}$	DC Current Gain	100	500		$V_{CE} = 10 \text{ V } I_C = 10 \text{ mA}$
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		0.25	V	$I_C = 10 \text{ mA } I_B = 1.0 \text{ mA}$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		0.8	V	$I_C = 10 \text{ mA } I_B = 1.0 \text{ mA}$
$V_{BE(on)}$	Base -Emitter On Voltage	0.5	1.2	V	$V_{CE} = 10 \text{ V } I_C = 10 \text{ mA}$

# 2N6076

## SILICON PNP SMALL SIGNAL TRANSISTOR

**ELECTRICAL CHARACTERISTICS** Con't (25 Degrees C Ambient Temperature unless otherwise stated)

<b>SYM</b>	<b>CHARACTERISTICS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>	<b>TEST CONDITIONS</b>
C <sub>cb</sub>	Output Capacitance	1	13	pF	V <sub>CB</sub> = 10 V, f = 1 MHz
h <sub>fe</sub>	Small Signal Current Gain	100	750		V <sub>CE</sub> = 10 V, I <sub>C</sub> =10 mA, f=1KHz

NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3. These ratings are based on a maximum junction temperature of 150 degrees C.